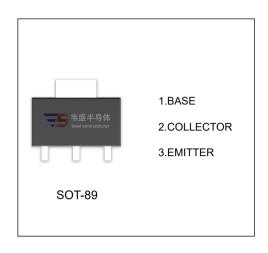


KTA1663 TRANSISTOR (PNP)

FEATURES

- High current applications
- Complementary to KTC4375



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-30	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current	-1.5	Α
Pc	Collector Power Dissipation	500	mW
R _{OJA}	Thermal Resistance From Junction To Ambient	250	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA, I _E =0	-30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I_E =-1mA, I_C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-0.5A	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1.5A, I _B =-30mA			-2	V
Base-emitter voltage	V_{BE}	V _{CE} =-2V, I _C =-0.5A			-1	V
Transition frequency	f _T	V _{CE} =-2V, I _C =-500mA		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0,f=1MHz			50	MHz

CLASSIFICATION OF hfe

Rank	0	Y
Range	100-200	160-320
Marking	НО	HY



